REPORT DOCUMENTATION PAGE

Form Approved OMB No. 0704-0188

Public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington, VA 22202-4302, and to the Office of Management and Budget, Paperwork Reduction Project (0704-0188), Washington, DC 20503.

1. AGENCY USE ONLY (Leave blank) 2. REPORT DATE 3. REPORT TY		3. REPORT TYPE AND DA	TES COVERED
December 20, 2002 Final Technical R		Final Technical Report	
4. TITLE AND SUBTITLE		6. F	UNDING NUMBERS
No. 1 Comment	American St.		00014-02- M-0115
Nanoimprint Lithography of Paralle	el Patterning of Nanoscale Magnetoel	ectronic Devices	
6. AUTHOR(S)		-	
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Office of Naval Reseach		'	AGENCY REPORT NUMBER
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11. SUPPLEMENTARY NOTES		<u> </u>	
The views, opinions and/or findings contained in this report are those of the author(s) and should not be construed as an official			
Department of the Army position, policy or decision, unless so designated by the documentation			
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12a. DISTRIBUTION AVAILABILITY		12b.	. DISTRIBUTION CODE
Approved for public release; dist	unununted		
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43 ADSTDACT ///	46)		
13. ABSTRACT (Maximum 200 words) Final technical report			
Final technical report.			
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14. SUBJECT TERMS			15. NUMBER OF PAGES
			16. PRICE CODE
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17. SECURITY CLASSIFICATION	18. SECURITY CLASSIFICATION	19, SECURITY OF ASSISTED AT	ION 20. LIMITATION OF ABSTRACT
OF REPORT	OF THIS PAGE	OF ABSTRACT	ADSTRACT
Unclassified	Unclassified	Unclassified	UL



Final Report to Office of Naval Research

Project: "Nanoimprint Lithography of Parallel Patterning of Nanoscale Magnetoelectronic Devices"

Supported by ONR (Contract #: N00014-02-M-0115, Manager Dr. Kristl Hathaway)

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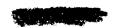
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Work Progress:

In the last 6 months, Nanonex Corp has developed technologies based on nanoimprint lithography for parallel patterning of nanoscale magnetoelectronic devices. The details are discussed in the following.

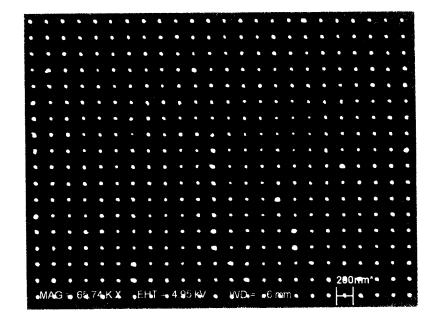
- (a) Nanonex Corp. has fabricated NIL masks with pillars that have diameters from 20 nm to 50 nm and height as large as 80 nm. Different mask materials, such as SiO₂ wafer and glass wafer, were used. Figure 1 shows the SEM and AFM images of masks with pillars patterns.
- (b) Nanonex Corp. has tested new NIL resists for sub-50 nm patterning. One example is double-layer resist, which is very good for small pattern imprint. As we know that the small patterns on the mask cannot be very high otherwise they could be broken during imprint process. The top resist in our double-layer resist has a much lower etch rate than the bottom. This can allow us to imprint the patterns into a very thin top resist, then transfer the patterns into the bottom layer which can be thicker and make the lift-off easier.

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- (c) Nanonex Corp. has patterned Co/Cu/Co magnetic multilayer. The patterns are dots with diameter around 50 nm, as shown in Fig. 2. Scanning electrical microscope and atomic force microscope were used to characterize the samples.
- (d) Nanonex Corp. has built NIL tools that have many advantages, such as excellent uniformity over 4-inch wafer, and machine cycle times of less than 1 minute. Figure 3 shows a photograph of an NIL machine built by Nanonex Corp.
- (e) Nanonex Corp. has studied the electro-deposition in nano holes. Several electrolytes have been tested. For the electrolyte which includes CoSO₄, CuSO₄ and H₃BO₃, first, the deposition rate of Co and Cu was calibrated. Then multilayer of Co/Cu was deposited. Co was deposited at potential of 1.4 V and period from 0.01 seconds to 0.04 seconds, and Cu was deposited at potential of 0.3 V and period of around 5 seconds. SEM and AFM images show that the deposition multilayer looks good. It was found that the deposition rate depends on the pattern size and area.





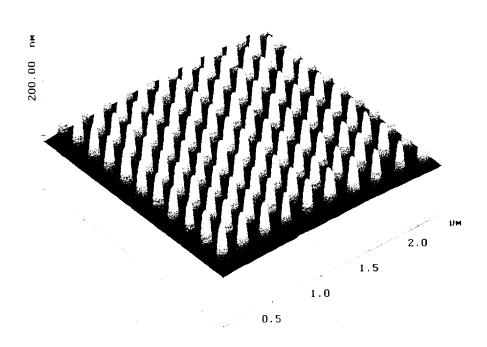
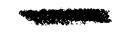


Fig. 1 SEM and AFM images of NIL mask with sub-50 nm pillars. SEM shows the pillar size is around 40 nm and AFM shows the pillar height is around 70 nm.



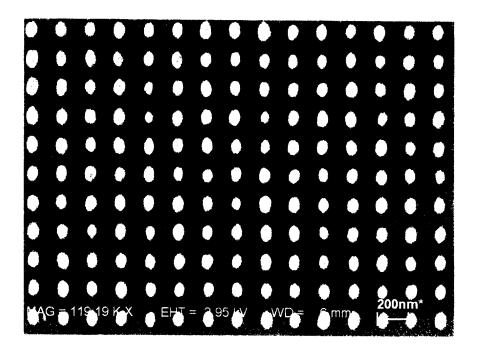


Fig. 2 SEM image of Co/Cu/Co magnetic multilayer patterned by double-layer resist.

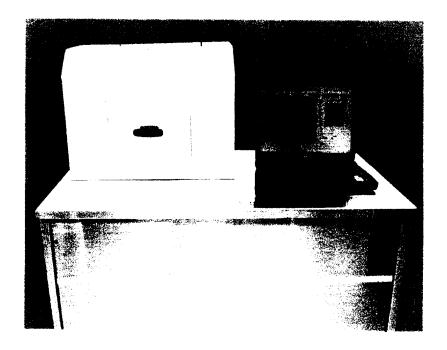


Fig. 3 The NIL machine built by Nanonex Corp.